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Understanding [Embedded - CPLDs \(Complex Programmable Logic Devices\)](#)

Embedded - CPLDs, or Complex Programmable Logic Devices, are highly versatile digital logic devices used in electronic systems. These programmable components are designed to perform complex logical operations and can be customized for specific applications. Unlike fixed-function ICs, CPLDs offer the flexibility to reprogram their configuration, making them an ideal choice for various embedded systems. They consist of a set of logic gates and programmable interconnects, allowing designers to implement complex logic circuits without needing custom hardware.

Applications of Embedded - CPLDs

Details

Product Status	Active
Programmable Type	In System Programmable
Delay Time tpd(1) Max	5.4 ns
Voltage Supply - Internal	2.5V, 3.3V
Number of Logic Elements/Blocks	570
Number of Macrocells	440
Number of Gates	-
Number of I/O	76
Operating Temperature	0°C ~ 85°C (TJ)
Mounting Type	Surface Mount
Package / Case	100-TQFP
Supplier Device Package	100-TQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epm570t100c4n

Table 2-1. MAX II Device Resources

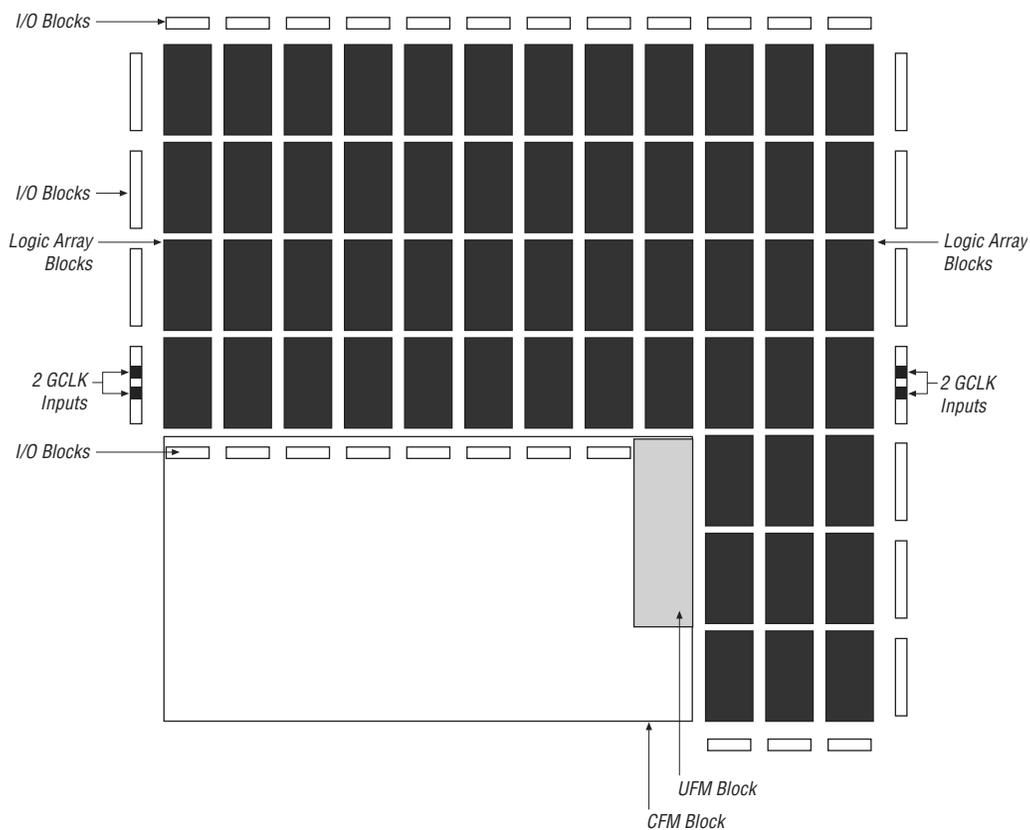
Devices	UFM Blocks	LAB Columns	LAB Rows		Total LABs
			Long LAB Rows	Short LAB Rows (Width) (1)	
EPM240	1	6	4	—	24
EPM570	1	12	4	3 (3)	57
EPM1270	1	16	7	3 (5)	127
EPM2210	1	20	10	3 (7)	221

Note to Table 2-1:

- (1) The width is the number of LAB columns in length.

Figure 2-2 shows a floorplan of a MAX II device.

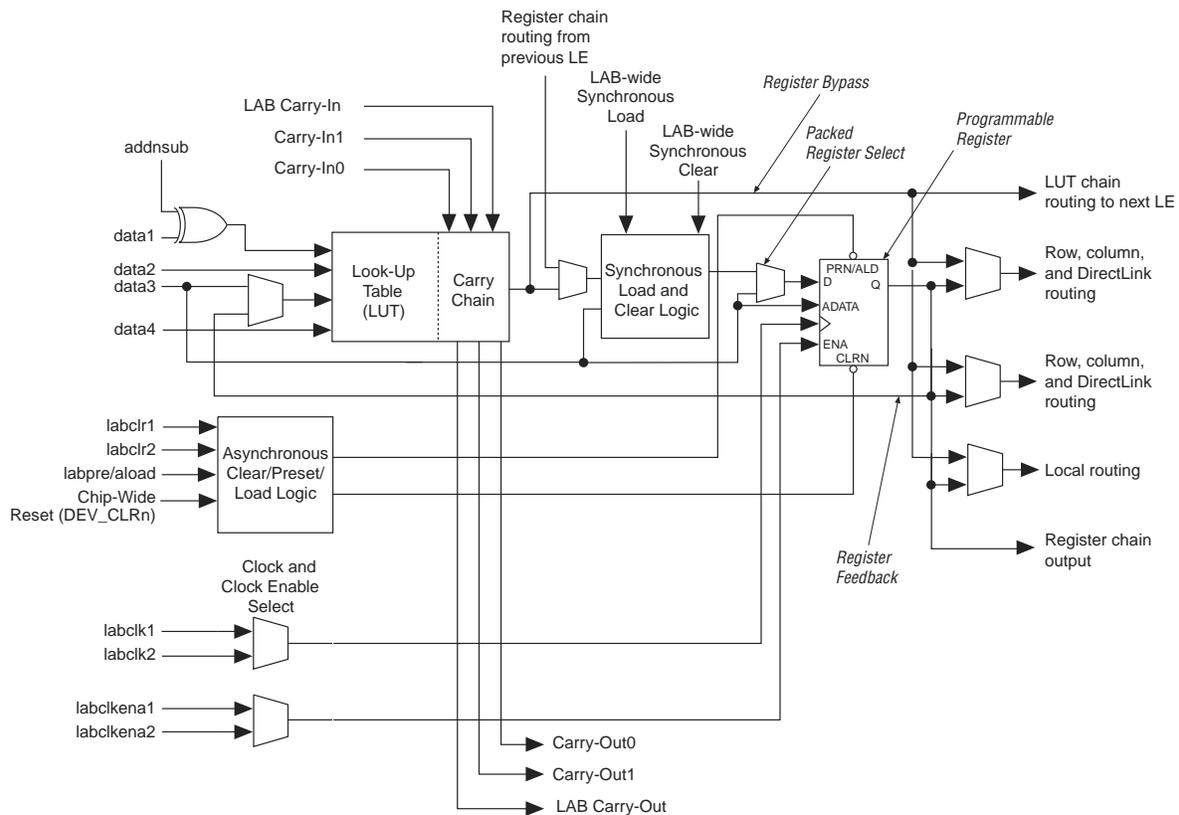
Figure 2-2. MAX II Device Floorplan (Note 1)



Note to Figure 2-2:

- (1) The device shown is an EPM570 device. EPM1270 and EPM2210 devices have a similar floorplan with more LABs. For EPM240 devices, the CFM and UFM blocks are located on the left side of the device.

Figure 2-6. MAX II LE



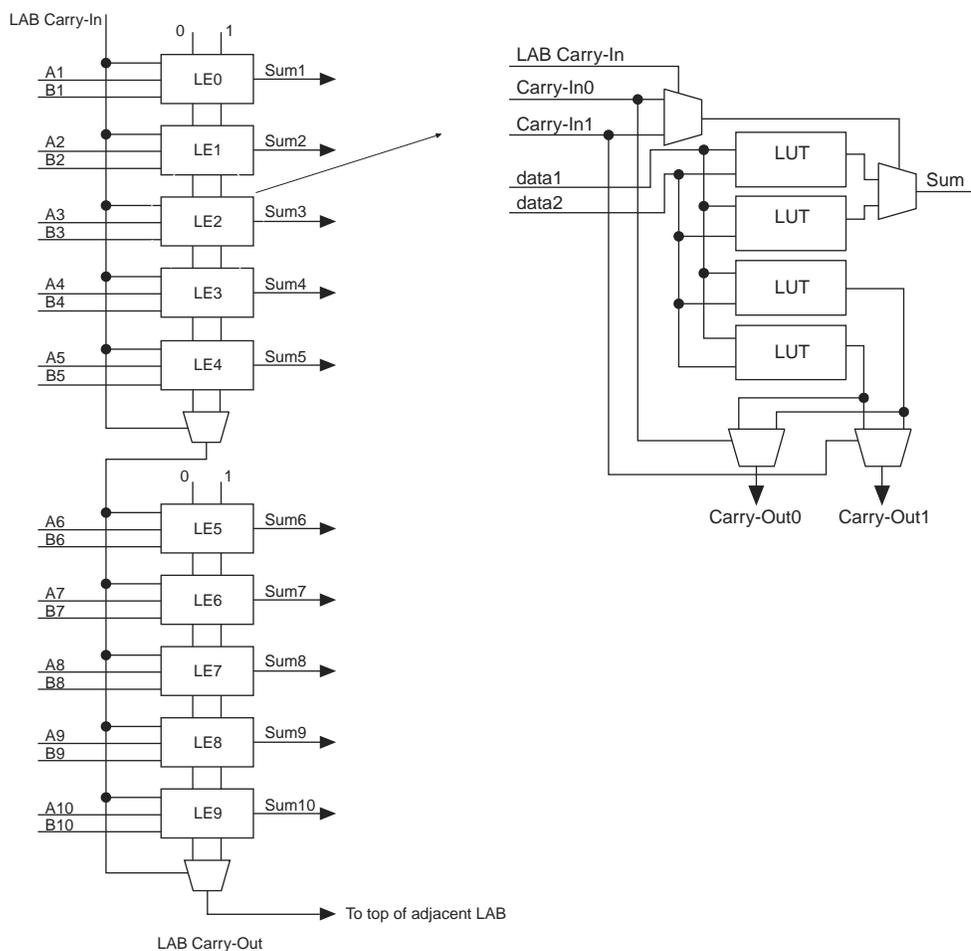
Each LE's programmable register can be configured for D, T, JK, or SR operation. Each register has data, true asynchronous load data, clock, clock enable, clear, and asynchronous load/preset inputs. Global signals, general-purpose I/O pins, or any LE can drive the register's clock and clear control signals. Either general-purpose I/O pins or LEs can drive the clock enable, preset, asynchronous load, and asynchronous data. The asynchronous load data input comes from the data3 input of the LE. For combinational functions, the LUT output bypasses the register and drives directly to the LE outputs.

Each LE has three outputs that drive the local, row, and column routing resources. The LUT or register output can drive these three outputs independently. Two LE outputs drive column or row and DirectLink routing connections and one drives local interconnect resources. This allows the LUT to drive one output while the register drives another output. This register packing feature improves device utilization because the device can use the register and the LUT for unrelated functions. Another special packing mode allows the register output to feed back into the LUT of the same LE so that the register is packed with its own fan-out LUT. This provides another mechanism for improved fitting. The LE can also drive out registered and unregistered versions of the LUT output.

The speed advantage of the carry-select chain is in the parallel precomputation of carry chains. Since the LAB carry-in selects the precomputed carry chain, not every LE is in the critical path. Only the propagation delays between LAB carry-in generation (LE 5 and LE 10) are now part of the critical path. This feature allows the MAX II architecture to implement high-speed counters, adders, multipliers, parity functions, and comparators of arbitrary width.

Figure 2-9 shows the carry-select circuitry in an LAB for a 10-bit full adder. One portion of the LUT generates the sum of two bits using the input signals and the appropriate carry-in bit; the sum is routed to the output of the LE. The register can be bypassed for simple adders or used for accumulator functions. Another portion of the LUT generates carry-out bits. An LAB-wide carry-in bit selects which chain is used for the addition of given inputs. The carry-in signal for each chain, carry-in0 or carry-in1, selects the carry-out to carry forward to the carry-in signal of the next-higher-order bit. The final carry-out signal is routed to an LE, where it is fed to local, row, or column interconnects.

Figure 2-9. Carry-Select Chain



The UFM block communicates with the logic array similar to LAB-to-LAB interfaces. The UFM block connects to row and column interconnects and has local interconnect regions driven by row and column interconnects. This block also has DirectLink interconnects for fast connections to and from a neighboring LAB. For more information about the UFM interface to the logic array, see “User Flash Memory Block” on page 2-18.

Table 2-2 shows the MAX II device routing scheme.

Table 2-2. MAX II Device Routing Scheme

Source	Destination										
	LUT Chain	Register Chain	Local (1)	DirectLink (1)	R4 (1)	C4 (1)	LE	UFM Block	Column IOE	Row IOE	Fast I/O (1)
LUT Chain	—	—	—	—	—	—	✓	—	—	—	—
Register Chain	—	—	—	—	—	—	✓	—	—	—	—
Local Interconnect	—	—	—	—	—	—	✓	✓	✓	✓	—
DirectLink Interconnect	—	—	✓	—	—	—	—	—	—	—	—
R4 Interconnect	—	—	✓	—	✓	✓	—	—	—	—	—
C4 Interconnect	—	—	✓	—	✓	✓	—	—	—	—	—
LE	✓	✓	✓	✓	✓	✓	—	—	✓	✓	✓
UFM Block	—	—	✓	✓	✓	✓	—	—	—	—	—
Column IOE	—	—	—	—	—	✓	—	—	—	—	—
Row IOE	—	—	—	✓	✓	✓	—	—	—	—	—

Note to Table 2-2:

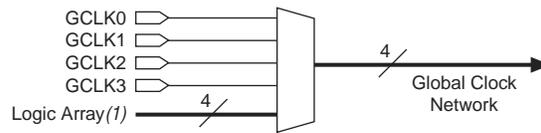
(1) These categories are interconnects.

Global Signals

Each MAX II device has four dual-purpose dedicated clock pins (GCLK[3..0], two pins on the left side and two pins on the right side) that drive the global clock network for clocking, as shown in Figure 2-13. These four pins can also be used as general-purpose I/O if they are not used to drive the global clock network.

The four global clock lines in the global clock network drive throughout the entire device. The global clock network can provide clocks for all resources within the device including LEs, LAB local interconnect, IOEs, and the UFM block. The global clock lines can also be used for global control signals, such as clock enables, synchronous or asynchronous clears, presets, output enables, or protocol control signals such as TRDY and IRDY for PCI. Internal logic can drive the global clock network for internally-generated global clocks and control signals. Figure 2-13 shows the various sources that drive the global clock network.

Figure 2-13. Global Clock Generation



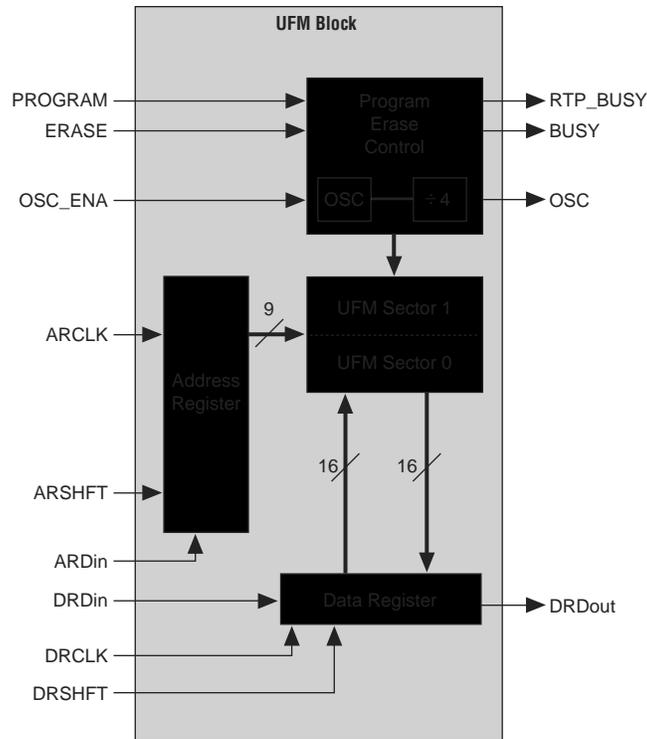
Note to Figure 2-13:

(1) Any I/O pin can use a MultiTrack interconnect to route as a logic array-generated global clock signal.

The global clock network drives to individual LAB column signals, LAB column clocks [3..0], that span an entire LAB column from the top to the bottom of the device. Unused global clocks or control signals in a LAB column are turned off at the LAB column clock buffers shown in Figure 2-14. The LAB column clocks [3..0] are multiplexed down to two LAB clock signals and one LAB clear signal. Other control signal types route from the global clock network into the LAB local interconnect. See “LAB Control Signals” on page 2-5 for more information.

- Auto-increment addressing
- Serial interface to logic array with programmable interface

Figure 2-15. UFM Block and Interface Signals



UFM Storage

Each device stores up to 8,192 bits of data in the UFM block. Table 2-3 shows the data size, sector, and address sizes for the UFM block.

Table 2-3. UFM Array Size

Device	Total Bits	Sectors	Address Bits	Data Width
EPM240	8,192	2	9	16
EPM570		(4,096 bits/sector)		
EPM1270				
EPM2210				

There are 512 locations with 9-bit addressing ranging from 000h to 1FFh. Sector 0 address space is 000h to 0FFh and Sector 1 address space is from 100h to 1FFh. The data width is up to 16 bits of data. The Quartus II software automatically creates logic to accommodate smaller read or program data widths. Erasure of the UFM involves individual sector erasing (that is, one erase of sector 0 and one erase of sector 1 is required to erase the entire UFM block). Since sector erase is required before a program or write, having two sectors enables a sector size of data to be left untouched while the other sector is erased and programmed with new data.

Internal Oscillator

As shown in Figure 2–15, the dedicated circuitry within the UFM block contains an oscillator. The dedicated circuitry uses this internally for its read and program operations. This oscillator's divide by 4 output can drive out of the UFM block as a logic interface clock source or for general-purpose logic clocking. The typical OSC output signal frequency ranges from 3.3 to 5.5 MHz, and its exact frequency of operation is not programmable.

Program, Erase, and Busy Signals

The UFM block's dedicated circuitry automatically generates the necessary internal program and erase algorithm once the PROGRAM or ERASE input signals have been asserted. The PROGRAM or ERASE signal must be asserted until the busy signal deasserts, indicating the UFM internal program or erase operation has completed. The UFM block also supports JTAG as the interface for programming and/or reading.

 For more information about programming and erasing the UFM block, refer to the *Using User Flash Memory in MAX II Devices* chapter in the *MAX II Device Handbook*.

Auto-Increment Addressing

The UFM block supports standard read or stream read operations. The stream read is supported with an auto-increment address feature. Deasserting the ARSHIFT signal while clocking the ARCLK signal increments the address register value to read consecutive locations from the UFM array.

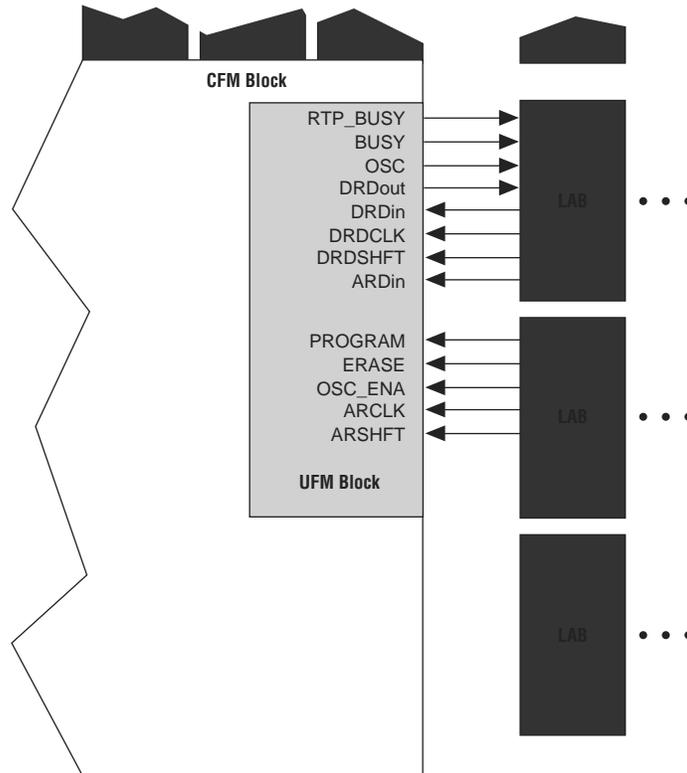
Serial Interface

The UFM block supports a serial interface with serial address and data signals. The internal shift registers within the UFM block for address and data are 9 bits and 16 bits wide, respectively. The Quartus II software automatically generates interface logic in LEs for a parallel address and data interface to the UFM block. Other standard protocol interfaces such as SPI are also automatically generated in LE logic by the Quartus II software.

 For more information about the UFM interface signals and the Quartus II LE-based alternate interfaces, refer to the *Using User Flash Memory in MAX II Devices* chapter in the *MAX II Device Handbook*.

UFM Block to Logic Array Interface

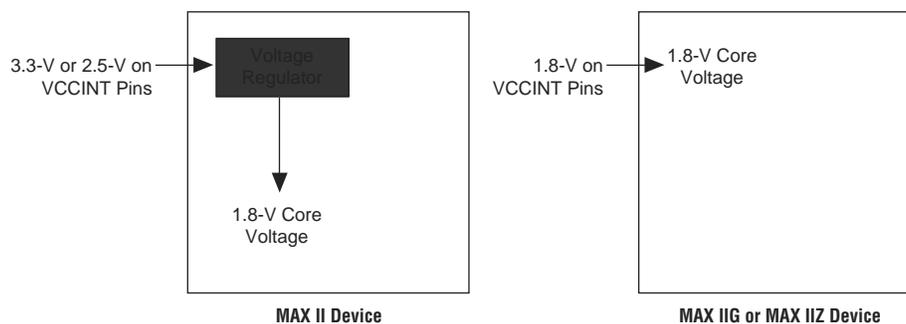
The UFM block is a small partition of the flash memory that contains the CFM block, as shown in Figure 2–1 and Figure 2–2. The UFM block for the EPM240 device is located on the left side of the device adjacent to the left most LAB column. The UFM block for the EPM570, EPM1270, and EPM2210 devices is located at the bottom left of the device. The UFM input and output signals interface to all types of interconnects (R4 interconnect, C4 interconnect, and DirectLink interconnect to/from adjacent LAB rows). The UFM signals can also be driven from global clocks, GCLK[3..0]. The interface region for the EPM240 device is shown in Figure 2–16. The interface regions for EPM570, EPM1270, and EPM2210 devices are shown in Figure 2–17.

Figure 2-17. EPM570, EPM1270, and EPM2210 UFM Block LAB Row Interface

MultiVolt Core

The MAX II architecture supports the MultiVolt core feature, which allows MAX II devices to support multiple V_{CC} levels on the V_{CCINT} supply. An internal linear voltage regulator provides the necessary 1.8-V internal voltage supply to the device. The voltage regulator supports 3.3-V or 2.5-V supplies on its inputs to supply the 1.8-V internal voltage to the device, as shown in Figure 2-18. The voltage regulator is not guaranteed for voltages that are between the maximum recommended 2.5-V operating voltage and the minimum recommended 3.3-V operating voltage.

The MAX IIG and MAX IIZ devices use external 1.8-V supply. The 1.8-V V_{CC} external supply powers the device core directly.

Figure 2-18. MultiVolt Core Feature in MAX II Devices

Document Revision History

Table 2-8 shows the revision history for this chapter.

Table 2-8. Document Revision History

Date and Revision	Changes Made	Summary of Changes
October 2008, version 2.2	<ul style="list-style-type: none"> ■ Updated Table 2-4 and Table 2-6. ■ Updated “I/O Standards and Banks” section. ■ Updated New Document Format. 	—
March 2008, version 2.1	<ul style="list-style-type: none"> ■ Updated “Schmitt Trigger” section. 	—
December 2007, version 2.0	<ul style="list-style-type: none"> ■ Updated “Clear and Preset Logic Control” section. ■ Updated “MultiVolt Core” section. ■ Updated “MultiVolt I/O Interface” section. ■ Updated Table 2-7. ■ Added “Referenced Documents” section. 	Updated document with MAX IIZ information.
December 2006, version 1.7	<ul style="list-style-type: none"> ■ Minor update in “Internal Oscillator” section. Added document revision history. 	—
August 2006, version 1.6	<ul style="list-style-type: none"> ■ Updated functional description and I/O structure sections. 	—
July 2006, version 1.5	<ul style="list-style-type: none"> ■ Minor content and table updates. 	—
February 2006, version 1.4	<ul style="list-style-type: none"> ■ Updated “LAB Control Signals” section. ■ Updated “Clear and Preset Logic Control” section. ■ Updated “Internal Oscillator” section. ■ Updated Table 2-5. 	—
August 2005, version 1.3	<ul style="list-style-type: none"> ■ Removed Note 2 from Table 2-7. 	—
December 2004, version 1.2	<ul style="list-style-type: none"> ■ Added a paragraph to page 2-15. 	—
June 2004, version 1.1	<ul style="list-style-type: none"> ■ Added CFM acronym. Corrected Figure 2-19. 	—

3. JTAG and In-System Programmability

Introduction

This chapter discusses how to use the IEEE Standard 1149.1 Boundary-Scan Test (BST) circuitry in MAX II devices and includes the following sections:

- “IEEE Std. 1149.1 (JTAG) Boundary-Scan Support” on page 3–1
- “In System Programmability” on page 3–4

IEEE Std. 1149.1 (JTAG) Boundary-Scan Support

All MAX® II devices provide Joint Test Action Group (JTAG) boundary-scan test (BST) circuitry that complies with the IEEE Std. 1149.1-2001 specification. JTAG boundary-scan testing can only be performed at any time after V_{CCINT} and all V_{CCIO} banks have been fully powered and a t_{CONFIG} amount of time has passed. MAX II devices can also use the JTAG port for in-system programming together with either the Quartus® II software or hardware using Programming Object Files (.pof), Jam™ Standard Test and Programming Language (STAPL) Files (.jam), or Jam Byte-Code Files (.jbc).

The JTAG pins support 1.5-V, 1.8-V, 2.5-V, or 3.3-V I/O standards. The supported voltage level and standard are determined by the V_{CCIO} of the bank where it resides. The dedicated JTAG pins reside in Bank 1 of all MAX II devices.

MAX II devices support the JTAG instructions shown in Table 3–1.

Table 3–1. MAX II JTAG Instructions (Part 1 of 2)

JTAG Instruction	Instruction Code	Description
SAMPLE/PRELOAD	00 0000 0101	Allows a snapshot of signals at the device pins to be captured and examined during normal device operation, and permits an initial data pattern to be output at the device pins.
EXTEST (1)	00 0000 1111	Allows the external circuitry and board-level interconnects to be tested by forcing a test pattern at the output pins and capturing test results at the input pins.
BYPASS	11 1111 1111	Places the 1-bit bypass register between the TDI and TDO pins, which allows the BST data to pass synchronously through selected devices to adjacent devices during normal device operation.
USERCODE	00 0000 0111	Selects the 32-bit USERCODE register and places it between the TDI and TDO pins, allowing the USERCODE to be serially shifted out of TDO. This register defaults to all 1's if not specified in the Quartus II software.
IDCODE	00 0000 0110	Selects the IDCODE register and places it between TDI and TDO, allowing the IDCODE to be serially shifted out of TDO.
HIGHZ (1)	00 0000 1011	Places the 1-bit bypass register between the TDI and TDO pins, which allows the boundary scan test data to pass synchronously through selected devices to adjacent devices during normal device operation, while tri-stating all of the I/O pins.

Table 3-3. 32-Bit MAX II Device IDCODE (Part 2 of 2)

Device	Binary IDCODE (32 Bits) (1)				HEX IDCODE
	Version (4 Bits)	Part Number	Manufacturer Identity (11 Bits)	LSB (1 Bit) (2)	
EPM240Z	0000	0010 0000 1010 0101	000 0110 1110	1	0x020A50DD
EPM570Z	0000	0010 0000 1010 0110	000 0110 1110	1	0x020A60DD

Notes to Table 3-2:

- (1) The most significant bit (MSB) is on the left.
- (2) The IDCODE's least significant bit (LSB) is always 1.

- For JTAG AC characteristics, refer to the *DC and Switching Characteristics* chapter in the *MAX II Device Handbook*.
- For more information about JTAG BST, refer to the *IEEE 1149.1 (JTAG) Boundary-Scan Testing for MAX II Devices* chapter in the *MAX II Device Handbook*.

JTAG Block

The MAX II JTAG block feature allows you to access the JTAG TAP and state signals when either the USER0 or USER1 instruction is issued to the JTAG TAP. The USER0 and USER1 instructions bring the JTAG boundary-scan chain (TDI) through the user logic instead of the MAX II device's boundary-scan cells. Each USER instruction allows for one unique user-defined JTAG chain into the logic array.

Parallel Flash Loader

The JTAG block ability to interface JTAG to non-JTAG devices is ideal for general-purpose flash memory devices (such as Intel- or Fujitsu-based devices) that require programming during in-circuit test. The flash memory devices can be used for FPGA configuration or be part of system memory. In many cases, the MAX II device is already connected to these devices as the configuration control logic between the FPGA and the flash device. Unlike ISP-capable CPLD devices, bulk flash devices do not have JTAG TAP pins or connections. For small flash devices, it is common to use the serial JTAG scan chain of a connected device to program the non-JTAG flash device. This is slow and inefficient in most cases and impractical for large parallel flash devices. Using the MAX II device's JTAG block as a parallel flash loader, with the Quartus II software, to program and verify flash contents provides a fast and cost-effective means of in-circuit programming during test. Figure 3-1 shows MAX II being used as a parallel flash loader.

5. DC and Switching Characteristics

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Introduction

System designers must consider the recommended DC and switching conditions discussed in this chapter to maintain the highest possible performance and reliability of the MAX® II devices. This chapter contains the following sections:

- “Operating Conditions” on page 5–1
- “Power Consumption” on page 5–8
- “Timing Model and Specifications” on page 5–8

Operating Conditions

Table 5–1 through Table 5–12 provide information about absolute maximum ratings, recommended operating conditions, DC electrical characteristics, and other specifications for MAX II devices.

Absolute Maximum Ratings

Table 5–1 shows the absolute maximum ratings for the MAX II device family.

Table 5–1. MAX II Device Absolute Maximum Ratings (*Note 1*), (*2*)

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCINT}	Internal supply voltage (<i>3</i>)	With respect to ground	–0.5	4.6	V
V_{CCIO}	I/O supply voltage	—	–0.5	4.6	V
V_I	DC input voltage	—	–0.5	4.6	V
I_{OUT}	DC output current, per pin (<i>4</i>)	—	–25	25	mA
T_{STG}	Storage temperature	No bias	–65	150	°C
T_{AMB}	Ambient temperature	Under bias (<i>5</i>)	–65	135	°C
T_J	Junction temperature	TQFP and BGA packages under bias	—	135	°C

Notes to Table 5–1:

- (1) Refer to the *Operating Requirements for Altera Devices Data Sheet*.
- (2) Conditions beyond those listed in Table 5–1 may cause permanent damage to a device. Additionally, device operation at the absolute maximum ratings for extended periods of time may have adverse effects on the device.
- (3) Maximum V_{CCINT} for MAX II devices is 4.6 V. For MAX IIG and MAX IIZ devices, it is 2.4 V.
- (4) Refer to *AN 286: Implementing LED Drivers in MAX & MAX II Devices* for more information about the maximum source and sink current for MAX II devices.
- (5) Refer to Table 5–2 for information about “under bias” conditions.

Recommended Operating Conditions

Table 5–2 shows the MAX II device family recommended operating conditions.

Table 5–2. MAX II Device Recommended Operating Conditions

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCINT} (1)	3.3-V supply voltage for internal logic and ISP	MAX II devices	3.00	3.60	V
	2.5-V supply voltage for internal logic and ISP	MAX II devices	2.375	2.625	V
	1.8-V supply voltage for internal logic and ISP	MAX IIG and MAX IIZ devices	1.71	1.89	V
V_{CCIO} (1)	Supply voltage for I/O buffers, 3.3-V operation	—	3.00	3.60	V
	Supply voltage for I/O buffers, 2.5-V operation	—	2.375	2.625	V
	Supply voltage for I/O buffers, 1.8-V operation	—	1.71	1.89	V
	Supply voltage for I/O buffers, 1.5-V operation	—	1.425	1.575	V
V_I	Input voltage	(2), (3), (4)	–0.5	4.0	V
V_O	Output voltage	—	0	V_{CCIO}	V
T_J	Operating junction temperature	Commercial range	0	85	°C
		Industrial range	–40	100	°C
		Extended range (5)	–40	125	°C

Notes to Table 5–2:

- (1) MAX II device in-system programming and/or user flash memory (UFM) programming via JTAG or logic array is not guaranteed outside the recommended operating conditions (for example, if brown-out occurs in the system during a potential write/program sequence to the UFM, users are recommended to read back UFM contents and verify against the intended write data).
- (2) Minimum DC input is –0.5 V. During transitions, the inputs may undershoot to –2.0 V for input currents less than 100 mA and periods shorter than 20 ns.
- (3) During transitions, the inputs may overshoot to the voltages shown in the following table based upon input duty cycle. The DC case is equivalent to 100% duty cycle. For more information about 5.0-V tolerance, refer to the *Using MAX II Devices in Multi-Voltage Systems* chapter in the *MAX II Device Handbook*.

V_{IN}	Max. Duty Cycle
4.0 V	100% (DC)
4.1	90%
4.2	50%
4.3	30%
4.4	17%
4.5	10%
- (4) All pins, including clock, I/O, and JTAG pins, may be driven before V_{CCINT} and V_{CCIO} are powered.
- (5) For the extended temperature range of 100 to 125° C, MAX II UFM programming (erase/write) is only supported via the JTAG interface. UFM programming via the logic array interface is not guaranteed in this range.

Table 5-4. MAX II Device DC Electrical Characteristics (Note 1) (Part 2 of 2)

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
I_{PULLUP}	I/O pin pull-up resistor current when I/O is unprogrammed	—	—	—	300	μA
C_{IO}	Input capacitance for user I/O pin	—	—	—	8	μF
C_{GCLK}	Input capacitance for dual-purpose GCLK/user I/O pin	—	—	—	8	μF

Notes to Table 5-4:

- (1) Typical values are for $T_A = 25^\circ C$, $V_{CCINT} = 3.3$ or 2.5 V, and $V_{CCIO} = 1.5$ V, 1.8 V, 2.5 V, or 3.3 V.
- (2) This value is specified for normal device operation. The value may vary during power-up. This applies for all V_{CCIO} settings (3.3 , 2.5 , 1.8 , and 1.5 V).
- (3) $V_i =$ ground, no load, no toggling inputs.
- (4) Commercial temperature ranges from $0^\circ C$ to $85^\circ C$ with maximum current at $85^\circ C$.
- (5) Industrial temperature ranges from $-40^\circ C$ to $100^\circ C$ with maximum current at $100^\circ C$.
- (6) This value applies to commercial and industrial range devices. For extended temperature range devices, the $V_{SCHMITT}$ typical value is 300 mV for $V_{CCIO} = 3.3$ V and 120 mV for $V_{CCIO} = 2.5$ V.
- (7) The TCK input is susceptible to high pulse glitches when the input signal fall time is greater than 200 ns for all I/O standards.
- (8) This is a peak current value with a maximum duration of t_{CONFIG} time.
- (9) Pin pull-up resistance values will lower if an external source drives the pin higher than V_{CCIO} .

Table 5-6. 3.3-V LVCMOS Specifications (Part 2 of 2)

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{OH}	High-level output voltage	$V_{CCIO} = 3.0$, $I_{OH} = -0.1$ mA (1)	$V_{CCIO} - 0.2$	—	V
V_{OL}	Low-level output voltage	$V_{CCIO} = 3.0$, $I_{OL} = 0.1$ mA (1)	—	0.2	V

Table 5-7. 2.5-V I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCIO}	I/O supply voltage	—	2.375	2.625	V
V_{IH}	High-level input voltage	—	1.7	4.0	V
V_{IL}	Low-level input voltage	—	-0.5	0.7	V
V_{OH}	High-level output voltage	$I_{OH} = -0.1$ mA (1)	2.1	—	V
		$I_{OH} = -1$ mA (1)	2.0	—	V
		$I_{OH} = -2$ mA (1)	1.7	—	V
V_{OL}	Low-level output voltage	$I_{OL} = 0.1$ mA (1)	—	0.2	V
		$I_{OL} = 1$ mA (1)	—	0.4	V
		$I_{OL} = 2$ mA (1)	—	0.7	V

Table 5-8. 1.8-V I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCIO}	I/O supply voltage	—	1.71	1.89	V
V_{IH}	High-level input voltage	—	$0.65 \times V_{CCIO}$	2.25 (2)	V
V_{IL}	Low-level input voltage	—	-0.3	$0.35 \times V_{CCIO}$	V
V_{OH}	High-level output voltage	$I_{OH} = -2$ mA (1)	$V_{CCIO} - 0.45$	—	V
V_{OL}	Low-level output voltage	$I_{OL} = 2$ mA (1)	—	0.45	V

Table 5-9. 1.5-V I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCIO}	I/O supply voltage	—	1.425	1.575	V
V_{IH}	High-level input voltage	—	$0.65 \times V_{CCIO}$	$V_{CCIO} + 0.3$ (2)	V
V_{IL}	Low-level input voltage	—	-0.3	$0.35 \times V_{CCIO}$	V
V_{OH}	High-level output voltage	$I_{OH} = -2$ mA (1)	$0.75 \times V_{CCIO}$	—	V
V_{OL}	Low-level output voltage	$I_{OL} = 2$ mA (1)	—	$0.25 \times V_{CCIO}$	V

Notes to Table 5-5 through Table 5-9:

- (1) This specification is supported across all the programmable drive strength settings available for this I/O standard, as shown in the *MAX II Architecture* chapter (*I/O Structure* section) in the *MAX II Device Handbook*.
- (2) This maximum V_{IH} reflects the JEDEC specification. The MAX II input buffer can tolerate a V_{IH} maximum of 4.0, as specified by the V_I parameter in Table 5-2.

Table 5-16. IOE Internal Timing Microparameters

Symbol	Parameter	MAX II / MAX IIG						MAX IIZ						Unit
		-3 Speed Grade		-4 Speed Grade		-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
t_{FASTIO}	Data output delay from adjacent LE to I/O block	—	159	—	207	—	254	—	170	—	348	—	428	ps
t_{IN}	I/O input pad and buffer delay	—	708	—	920	—	1,132	—	907	—	970	—	986	ps
$t_{GLOB} (1)$	I/O input pad and buffer delay used as global signal pin	—	1,519	—	1,974	—	2,430	—	2,261	—	2,670	—	3,322	ps
t_{IOE}	Internally generated output enable delay	—	354	—	374	—	460	—	530	—	966	—	1,410	ps
t_{DL}	Input routing delay	—	224	—	291	—	358	—	318	—	410	—	509	ps
$t_{OD} (2)$	Output delay buffer and pad delay	—	1,064	—	1,383	—	1,702	—	1,319	—	1,526	—	1,543	ps
$t_{XZ} (3)$	Output buffer disable delay	—	756	—	982	—	1,209	—	1,045	—	1,264	—	1,276	ps
$t_{ZX} (4)$	Output buffer enable delay	—	1,003	—	1,303	—	1,604	—	1,160	—	1,325	—	1,353	ps

Notes to Table 5-16:

- (1) Delay numbers for t_{GLOB} differ for each device density and speed grade. The delay numbers for t_{GLOB} , shown in Table 5-16, are based on an EPM240 device target.
- (2) Refer to Table 5-32 and 5-24 for delay adders associated with different I/O standards, drive strengths, and slew rates.
- (3) Refer to Table 5-19 and 5-14 for t_{XZ} delay adders associated with different I/O standards, drive strengths, and slew rates.
- (4) Refer to Table 5-17 and 5-13 for t_{ZX} delay adders associated with different I/O standards, drive strengths, and slew rates.

Table 5-17 through Table 5-20 show the adder delays for t_{ZX} and t_{XZ} microparameters when using an I/O standard other than 3.3-V LVTTTL with 16 mA drive strength.

Table 5-17. t_{ZX} IOE Microparameter Adders for Fast Slew Rate (Part 1 of 2)

Standard		MAX II / MAX IIG						MAX IIZ						Unit
		-3 Speed Grade		-4 Speed Grade		-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
3.3-V LVTTTL	16 mA	—	0	—	0	—	0	—	0	—	0	—	0	ps
	8 mA	—	28	—	37	—	45	—	72	—	71	—	74	ps
3.3-V LVCMOS	8 mA	—	0	—	0	—	0	—	0	—	0	—	0	ps
	4 mA	—	28	—	37	—	45	—	72	—	71	—	74	ps
2.5-V LVTTTL / LVCMOS	14 mA	—	14	—	19	—	23	—	75	—	87	—	90	ps
	7 mA	—	314	—	409	—	503	—	162	—	174	—	177	ps
1.8-V LVTTTL / LVCMOS	6 mA	—	450	—	585	—	720	—	279	—	289	—	291	ps
	3 mA	—	1,443	—	1,876	—	2,309	—	499	—	508	—	512	ps

Table 5-20. t_{XZ} IOE Microparameter Adders for Slow Slew Rate

Standard		MAX II / MAX IIG						MAX IIZ						Unit
		-3 Speed Grade		-4 Speed Grade		-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
3.3-V LVTTTL	16 mA	—	206	—	-20	—	-247	—	1,433	—	1,446	—	1,454	ps
	8 mA	—	891	—	665	—	438	—	1,332	—	1,345	—	1,348	ps
3.3-V LVCMOS	8 mA	—	206	—	-20	—	-247	—	1,433	—	1,446	—	1,454	ps
	4 mA	—	891	—	665	—	438	—	1,332	—	1,345	—	1,348	ps
2.5-V LVTTTL / LVCMOS	14 mA	—	222	—	-4	—	-231	—	213	—	208	—	213	ps
	7 mA	—	943	—	717	—	490	—	166	—	161	—	166	ps
3.3-V PCI	20 mA	—	161	—	210	—	258	—	1,332	—	1,345	—	1,348	ps

 The default slew rate setting for MAX II devices in the Quartus II design software is “fast”.

Table 5-21. UFM Block Internal Timing Microparameters (Part 1 of 3)

Symbol	Parameter	MAX II / MAX IIG						MAX IIZ						Unit
		-3 Speed Grade		-4 Speed Grade		-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
t_{ACLK}	Address register clock period	100	—	100	—	100	—	100	—	100	—	100	—	ns
t_{ASU}	Address register shift signal setup to address register clock	20	—	20	—	20	—	20	—	20	—	20	—	ns
t_{AH}	Address register shift signal hold to address register clock	20	—	20	—	20	—	20	—	20	—	20	—	ns
t_{ADS}	Address register data in setup to address register clock	20	—	20	—	20	—	20	—	20	—	20	—	ns
t_{ADH}	Address register data in hold from address register clock	20	—	20	—	20	—	20	—	20	—	20	—	ns
t_{DCLK}	Data register clock period	100	—	100	—	100	—	100	—	100	—	100	—	ns
t_{DSS}	Data register shift signal setup to data register clock	60	—	60	—	60	—	60	—	60	—	60	—	ns
t_{DSH}	Data register shift signal hold from data register clock	20	—	20	—	20	—	20	—	20	—	20	—	ns

Table 5-21. UFM Block Internal Timing Microparameters (Part 2 of 3)

Symbol	Parameter	MAX II / MAX IIG						MAX IIZ						Unit
		-3 Speed Grade		-4 Speed Grade		-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
t_{DDs}	Data register data in setup to data register clock	20	—	20	—	20	—	20	—	20	—	20	—	ns
t_{DDH}	Data register data in hold from data register clock	20	—	20	—	20	—	20	—	20	—	20	—	ns
t_{DP}	Program signal to data clock hold time	0	—	0	—	0	—	0	—	0	—	0	—	ns
t_{PB}	Maximum delay between program rising edge to UFM busy signal rising edge	—	960	—	960	—	960	—	960	—	960	—	960	ns
t_{BP}	Minimum delay allowed from UFM busy signal going low to program signal going low	20	—	20	—	20	—	20	—	20	—	20	—	ns
t_{PPMX}	Maximum length of busy pulse during a program	—	100	—	100	—	100	—	100	—	100	—	100	μs
t_{AE}	Minimum erase signal to address clock hold time	0	—	0	—	0	—	0	—	0	—	0	—	ns
t_{EB}	Maximum delay between the erase rising edge to the UFM busy signal rising edge	—	960	—	960	—	960	—	960	—	960	—	960	ns
t_{BE}	Minimum delay allowed from the UFM busy signal going low to erase signal going low	20	—	20	—	20	—	20	—	20	—	20	—	ns
t_{EPMX}	Maximum length of busy pulse during an erase	—	500	—	500	—	500	—	500	—	500	—	500	ms
t_{DCO}	Delay from data register clock to data register output	—	5	—	5	—	5	—	5	—	5	—	5	ns

Referenced Documents

This chapter references the following document:

- *Package Information* chapter in the *MAX II Device Handbook*

Document Revision History

Table 6–1 shows the revision history for this chapter.

Table 6–1. Document Revision History

Date and Revision	Changes Made	Summary of Changes
August 2009, version 1.6	■ Updated Figure 6–1.	Added information for speed grade –8
October 2008, version 1.5	■ Updated New Document Format.	—
December 2007, version 1.4	■ Added “Referenced Documents” section. ■ Updated Figure 6–1.	Updated document with MAX IIZ information.
December 2006, version 1.3	■ Added document revision history.	—
October 2006, version 1.2	■ Updated Figure 6-1.	—
June 2005, version 1.1	■ Removed Dual Marking section.	—